



# 3CD103

## PNP Silicon Low Frequency High Power Transistor



### Features:

1. Heavy output current.Small saturation voltage drop. Good temperature stability.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611.
3. Use for power amplify, Low-speed switch, power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+.

### TECHNICAL DATA:

( $T_a = 25^\circ\text{C}$ )

| Parameter name                             | Symbols       | Unit             | Specifications    | Test Condition                      |
|--|---------------|------------------|-------------------|-------------------------------------|
| Collector-Emitter Voltage                  | $V_{CEO}$     | V                | 200               |                                     |
| Emitter-Base Voltage                       | $V_{EBO}$     | V                | 9                 |                                     |
| Max. Collector Current                     | $I_{CM}$      | A                | 10                |                                     |
| Max. Collector Dissipation                 | $P_{CM}$      | W                | 100               | ( $T_c:75^\circ\text{C}$ )          |
| Junction Temperature                       | $T_{jm}$      | $^\circ\text{C}$ | 175               |                                     |
| Storage Temperature                        | $T_{stg}$     | $^\circ\text{C}$ | -55~+175          |                                     |
| Collector-Emitter Leakage Current          | $I_{CEO}$     | mA               | 2.0               | $V_{CE}=10\text{V}$                 |
| Collector- Emitter Saturation Voltage Drop | $V_{CE(sat)}$ | V                | 1.0               | $I_C=3\text{A}, I_B=0.6\text{A}$    |
| DC Current Gain                            | $h_{FE}$      |                  | Min.:10, Max.:180 | $V_{CE}=5\text{V}, I_C=2.5\text{A}$ |
| Collector-Emitter Breakdown Voltage        | $V_{(BR)CEO}$ | V                | 200               | $I_C=10\text{mA}$                   |
| E-Base Breakdown Voltage                   | $V_{(BR)EBO}$ | V                | 9                 | $I_E=10\text{mA}$                   |

### Outline and Dimensions: